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Case No. 9905/40
Client No. BIF116533/US

UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:)
NGUYEN et al.)
Serial No.: Not Yet Assigned) Examiner:
Filing Date: Herewith) Not Yet Assigned
For: METHOD FOR SELF-SUPPORTED) Group Art Unit:
TRANSFER OF A FINE LAYER BY) Not Yet Assigned
PULSATION AFTER IMPLANTATION)
OR CO-IMPLANTATION)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

Dear Sir:

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following references:

U.S. AND FOREIGN REFERENCES

Patent/ Publication No.	Date of Issue/Publication	Patentee/Applicant/Country
US 2004/0144487 A1	07/29/2004	Martinez et al.
US 2003/0134489 A1	07/17/2003	Schwarzenbach et al.
US 2003/0077885 A1	04/24/2003	Aspar et al.
US 2002/0025604 A1	02/28/2003	Tiwari
US 6,593,212 B1	07/15/2003	Kub et al.
US 6,362,077 B1	03/26/2002	Aspar et al.
US 6,303,468 B1	10/16/2001	Aspar et al.
US 6,225,192	05/01/2001	Aspar et al.
US 6,020,252	02/01/2000	Aspar et al.
FR 2 767 416 A1	02/19/1999	France
FR 2 847 075 A1	05/14/2004	France
WO 2004/044976 A1	05/27/2004	PCT
WO 03/013815 A1	02/20/2003	PCT
WO 02/083387 A1	10/24/2002	PCT

WO 00/63965	10/26/2000	PCT
EP 0 994 503 A1	04/19/2000	EPO
EP 02 293 049 A1	05/20/1988	EPO
EP 02 293 049 B1	05/20/1988	EPO

OTHER ART

Argawal et al., "Efficient Production of Silicon-on-Insulator Films by Co-Implantation of He+ with H+," *Applied Physics Letters*, Volume 72, Number 9, 2 March 1998 ; pp. 1086-1088.

Cerofolini et al., *Materials Science and Engineering*, B71 - 2000, pp. 196-202.

Henttinen et al., *Applied Physics Letters*, Volume 16, Number 17, 24 April 2000; pp. 2370-2372.

For the Examiner's convenience, Applicants are enclosing Form PTO-1449 (one sheet) and copies of cited references A7-A14. Applicants respectfully request the Examiner's consideration of the above references and entry thereof into the record of this application.

In accordance with 37 C.F.R. §1.98(a)(3), the applicants state as follows:

FR 2 767 416 A1 relates to a method for making a thin film of solid material, comprising a step of ion implantation through a surface of said solid material substrate by means of ions. A non-certified English translation of the Abstract is enclosed herewith. Applicants have also cited the corresponding U.S. Patent No. 6,303,468 B1;

FR 2 847 075 A1 relates to the fabrication of a thin film, including a buried embrittled zone by implantation of a chemical species into a substrate for detachment of the thin film. A non-certified English translation of the Abstract is enclosed herewith;

EPO 0994503 relates to a structure and method for producing a thin layer including implantation to form microcavities. Applicants have also cited the corresponding U.S. Patent No. 6,362,077 B1;

WO 2004/044976 relates to a method for producing a thin layer including ion implantation to form an embrittled zone;

WO 03/013815 relates to a substrate detachment device and method for detaching substrates along a cleavage plane;

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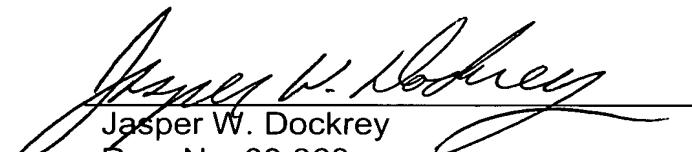
WO 02/083387 relates to a device and method for cutting substrates along an embrittled area. Applicants have also cited the corresponding U.S. Patent No. US 2004144487.

Also enclosed is a copy of the International Search Report dated April 5, 2005 for corresponding PCT Application No. WO2005/043615 A1.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,



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FORM PTO-1449	SERIAL NO. Not Yet Assigned	CASE NO. 407577175 9905/40 (BIF115433/US)
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE Herewith	GROUP ART UNIT Not Yet Assigned
	APPLICANTS: NGUYEN et al.	

REFERENCE DESIGNATION **U.S. PATENT DOCUMENTS**

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS/ SUBCLASS	FILING DATE
		Number-Kind Code (if known)				
	A1	US 2004/0144487 A1	07/29/2004	Martinez et al.		
	A2	US 2003/0134489 A1	07/17/2003	Schwarzenbach et al.		
	A3	US 2003/0077885 A1	04/24/2003	Aspar et al.		
	A4	US 2002/0025604 A1	02/28/2003	Tiwari		
	A5	US 6,593,212 B1	07/15/2003	Kub et al.		
	A6	US 6,362,077 B1	03/26/2002	Aspar et al.		
	A7	US 6,303,468 B1	10/16/2001	Aspar et al.		
	A8	US 6,225,192	05/01/2001	Aspar et al.		
	A9	US 6,020,252	02/01/2000	Aspar et al.		

FOREIGN PATENT DOCUMENTS

FOREIGN PATENT DOCUMENTS						
EXAMINER INITIAL		DOCUMENT NUMBER Number-Kind Code (if known)	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION YES OR NO
	A10	FR 2 847 075 A1	05/14/2004	France		Abstract
	A11	FR 2 767 416 A1	02/19/1999	France		Abstract
	A12	WO 2004/044976 A1	05/27/2004	PCT		Abstract
	A13	WO 03/013815 A1	02/20/2003	PCT		Abstract
	A14	WO 02/083387 A1	10/24/2002	PCT		Abstract
	A15	WO 00/63965	10/26/2000	PCT		
	A16	EP 0 994 503 A1	04/19/2000	EPO		Abstract
	A17	EP 02 293 049 A1	05/20/1988	EPO		
	A18	EP 02 293 049 B1	05/20/1988	EPO		

EXAMINER INITIAL	OTHER ART – NON PATENT LITERATURE DOCUMENTS (Include name of author, title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date page(s), volume-issue number(s), publisher, city and/or country where published.)	
	A19	Argawal et al., "Efficient Production of Silicon-on-Insulator Films by Co-Implantation of He+ with H+," <i>Applied Physics Letters</i> , Volume 72, Number 9, 2 March 1998 ; pp. 1086-1088.
	A20	Cerofolini et al., <i>Materials Science and Engineering</i> , B71 - 2000, pp. 196-202.
	A21	Henttinen et al., <i>Applied Physics Letters</i> , Volume 16, Number 17, 24 April 2000; pp. 2370-2372.

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609;
Draw line through citation if not in conformance and not considered. Include copy of this form with next
communication to applicant.